NTMD3N08, NTMD3N08L

Product Preview

80 V Power MOSFET

ON Semiconductor utilizes its latest MOSFET technology process to manufacture 80 V power MOSFET devices to achieve the lowest possible on–resistance per silicon area. These 80 V devices are designed for Power Management solutions in 42 V Automotive system applications. Typical applications include integrated starter alternator, electronic power steering, electronic fuel injection, catalytic converter heaters and other high power applications made possible via an automotive 42 V bus. ON Semiconductor's latest technology offering continues to offer high avalanche energy capability and low reverse recovery losses.



 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V(BR)DSS				Vdc	
$(V_{GS} = 0 \text{ Vdc}, I_{D} = 250 \mu\text{Adc})$		80	_	_		
Zero Gate Voltage Drain Current (VDS = 80 Vdc, VGS = 0 Vdc)	IDSS	_	_	1.0	μAdc	
(V _{DS} = 80 Vdc, V _{GS} = 0 Vdc, T _J =150°C)		_	-	10		
Gate-Body Leakage Current (VGS = ±20 Vdc, VDS = 0 Vdc)	IGSS	_	_	±100	nAdc	

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 250 μAdc) NTMD3N08 NTMD3N08L	VGS(th)	2.0 1.0	3.0 2.0	4.0 3.0	Vdc
Static Drain-to-Source On-Resistance (ID = 1.5 Adc) NTMD3N08, VGS= 10 V NTMD3N08L, VGS = 5 V	RDS(on)	-	185 200	1-1	mΩ



http://onsemi.com

3 AMPERES 3N08 Typ RDS(on) = 185 m Ω 3N08L Typ RDS(on) = 200 m Ω





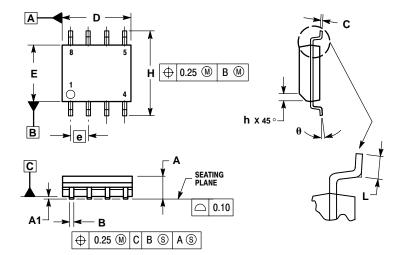
DUAL SO-8 CASE 751 STYLE 11

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

NTMD3N08, NTMD3N08L

PACKAGE DIMENSIONS

DUAL SO-8 CASE 751-06 **ISSUE T**



NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
- DIMENSIONS ARE IN MILLIMETER.
- DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
В	0.35	0.49		
С	0.19	0.25		
D	4.80	5.00		
E	3.80	4.00		
е	1.27 BSC			
Н	5.80	6.20		
h	0.25	0.50		
L	0.40	1.25		
A	n۰	7 °		

STYLE 11:

SOURCE 1

- GATE 1 2.
- SOURCE 2 3.
- GATE 2
- 5 DRAIN 2 DRAIN 2
- 6. DRAIN 1
- DRAIN 1

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